

Yasuhiko Arakawa

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626

papers

22,186

citations

66

h-index

128

g-index

671

ext. papers

25,014

ext. citations

3.3

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6.87

L-index

| # | Paper | IF | Citations |
|-----|--|------|-----------|
| 626 | Multidimensional quantum well laser and temperature dependence of its threshold current. <i>Applied Physics Letters</i> , 1982 , 40, 939-941 | 3.4 | 2694 |
| 625 | Observation of the coupled exciton-photon mode splitting in a semiconductor quantum microcavity. <i>Physical Review Letters</i> , 1992 , 69, 3314-3317 | 7.4 | 1840 |
| 624 | Quantum well lasers--Gain, spectra, dynamics. <i>IEEE Journal of Quantum Electronics</i> , 1986 , 22, 1887-1899 | 2 | 456 |
| 623 | A gallium nitride single-photon source operating at 200 K. <i>Nature Materials</i> , 2006 , 5, 887-92 | 27 | 339 |
| 622 | Efficient Carrier Relaxation Mechanism in InGaAs/GaAs Self-Assembled Quantum Dots Based on the Existence of Continuum States. <i>Physical Review Letters</i> , 1999 , 82, 4114-4117 | 7.4 | 316 |
| 621 | Room-temperature triggered single photon emission from a III-nitride site-controlled nanowire quantum dot. <i>Nano Letters</i> , 2014 , 14, 982-6 | 11.5 | 285 |
| 620 | Rapid carrier relaxation in self-assembled In _x Ga _{1-x} As/GaAs quantum dots. <i>Physical Review B</i> , 1996 , 54, 11532-11538 | 3.3 | 260 |
| 619 | Laser oscillation in a strongly coupled single-quantum-dot nanocavity system. <i>Nature Physics</i> , 2010 , 6, 279-283 | 16.2 | 247 |
| 618 | Fabrication of InAs/GaAs quantum dot solar cells with enhanced photocurrent and without degradation of open circuit voltage. <i>Applied Physics Letters</i> , 2010 , 96, 203507 | 3.4 | 217 |
| 617 | Theory of gain, modulation response, and spectral linewidth in AlGaAs quantum well lasers. <i>IEEE Journal of Quantum Electronics</i> , 1985 , 21, 1666-1674 | 2 | 216 |
| 616 | Over 1.5 h light emission from InAs quantum dots embedded in InGaAs strain-reducing layer grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2001 , 78, 3469-3471 | 3.4 | 209 |
| 615 | Room temperature lasing at blue wavelengths in gallium nitride microcavities. <i>Science</i> , 1999 , 285, 1905-1908 | 33.3 | 203 |
| 614 | Highly uniform InGaAs/GaAs quantum dots (~15 nm) by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 1994 , 65, 1421-1423 | 3.4 | 202 |
| 613 | Quantum noise and dynamics in quantum well and quantum wire lasers. <i>Applied Physics Letters</i> , 1984 , 45, 950-952 | 3.4 | 199 |
| 612 | Recent progress in self-assembled quantum-dot optical devices for optical telecommunication: temperature-insensitive 10 Gb/s directly modulated lasers and 40 Gb/s signal-regenerative amplifiers. <i>Journal Physics D: Applied Physics</i> , 2005 , 38, 2126-2134 | 3 | 177 |
| 611 | Nanometer-scale InGaN self-assembled quantum dots grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 1999 , 74, 383-385 | 3.4 | 177 |
| 610 | Phonon bottleneck in quantum dots: Role of lifetime of the confined optical phonons. <i>Physical Review B</i> , 1999 , 59, 5069-5073 | 3.3 | 165 |

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| 609 | Time-resolved vacuum Rabi oscillations in a semiconductor quantum microcavity. <i>Physical Review B</i> , 1994 , 50, 14663-14666 | 3.3 | 165 |
| 608 | In situ fabrication of self-aligned InGaAs quantum dots on GaAs multiatomic steps by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 1995 , 66, 3663-3665 | 3.4 | 152 |
| 607 | Pentacene-based organic field-effect transistors. <i>Journal of Physics Condensed Matter</i> , 2008 , 20, 184011 | 1.8 | 150 |
| 606 | An ultrawide-band semiconductor optical amplifier having an extremely high penalty-free output power of 23 dBm achieved with quantum dots. <i>IEEE Photonics Technology Letters</i> , 2005 , 17, 1614-1616 | 2.2 | 149 |
| 605 | Fabrication of GaAs quantum wires on epitaxially grown V grooves by metal-organic chemical-vapor deposition. <i>Journal of Applied Physics</i> , 1992 , 71, 533-535 | 2.5 | 149 |
| 604 | Lasing oscillation in a three-dimensional photonic crystal nanocavity with a complete bandgap. <i>Nature Photonics</i> , 2011 , 5, 91-94 | 33.9 | 143 |
| 603 | Room temperature continuous-wave lasing in photonic crystal nanocavity. <i>Optics Express</i> , 2006 , 14, 6308-6315 | 3.5 | 143 |
| 602 | Coupling of quantum-dot light emission with a three-dimensional photonic-crystal nanocavity. <i>Nature Photonics</i> , 2008 , 2, 688-692 | 33.9 | 142 |
| 601 | Photonic crystal nanocavity based on a topological corner state. <i>Optica</i> , 2019 , 6, 786 | 8.6 | 141 |
| 600 | Room-temperature lasing in a single nanowire with quantum dots. <i>Nature Photonics</i> , 2015 , 9, 501-505 | 33.9 | 132 |
| 599 | Photoluminescence spectra and anisotropic energy shift of GaAs quantum wires in high magnetic fields. <i>Physical Review Letters</i> , 1992 , 69, 2963-2966 | 7.4 | 130 |
| 598 | Temperature-Insensitive Eye-Opening under 10-Gb/s Modulation of 1.3- μ m P-Doped Quantum-Dot Lasers without Current Adjustments. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, L1124-L1126 | 1.4 | 128 |
| 597 | Structural and optical properties of type II GaSb/GaAs self-assembled quantum dots grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1999 , 85, 8349-8352 | 2.5 | 121 |
| 596 | Narrow photoluminescence peaks from localized states in InGaN quantum dot structures. <i>Applied Physics Letters</i> , 2000 , 76, 2361-2363 | 3.4 | 118 |
| 595 | Si Photonic Wire Waveguide Devices. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2006 , 12, 1371-1379 | 3.8 | 110 |
| 594 | High-density and size-controlled GaN self-assembled quantum dots grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2002 , 80, 3937-3939 | 3.4 | 108 |
| 593 | Ectopically expressed PDX-1 in liver initiates endocrine and exocrine pancreas differentiation but causes dysmorphogenesis. <i>Biochemical and Biophysical Research Communications</i> , 2003 , 310, 1017-25 | 3.4 | 106 |
| 592 | Single-Photon Generation in the 1.55- μ m Optical-Fiber Band from an InAs/InP Quantum Dot. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, L620-L622 | 1.4 | 106 |

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| 591 | Organic light-emitting diodes driven by pentacene-based thin-film transistors. <i>Applied Physics Letters</i> , 2003 , 83, 3410-3412 | 3.4 | 103 |
| 590 | Quantum key distribution over 120 km using ultrahigh purity single-photon source and superconducting single-photon detectors. <i>Scientific Reports</i> , 2015 , 5, 14383 | 4.9 | 101 |
| 589 | Compact 1 x N thermo-optic switches based on silicon photonic wire waveguides. <i>Optics Express</i> , 2005 , 13, 10109-14 | 3.3 | 101 |
| 588 | Progress in GaN-based quantum dots for optoelectronics applications. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2002 , 8, 823-832 | 3.8 | 100 |
| 587 | Photonic crystal nanocavity laser with a single quantum dot gain. <i>Optics Express</i> , 2009 , 17, 15975-82 | 3.3 | 96 |
| 586 | Spontaneous two-photon emission from a single quantum dot. <i>Physical Review Letters</i> , 2011 , 107, 233607-4 | 3.4 | 95 |
| 585 | Atomic structure and phase stability of In _x Ga _{1-x} N random alloys calculated using a valence-force-field method. <i>Physical Review B</i> , 1999 , 60, 1701-1706 | 3.3 | 95 |
| 584 | A Hybrid Integrated Light Source on a Silicon Platform Using a Trident Spot-Size Converter. <i>Journal of Lightwave Technology</i> , 2014 , 32, 1329-1336 | 4 | 94 |
| 583 | Highly reflective GaN/Al _{0.34} Ga _{0.66} N quarter-wave reflectors grown by metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , 1998 , 73, 3653-3655 | 3.4 | 94 |
| 582 | Selective growth of InGa _N quantum dot structures and their microphotoluminescence at room temperature. <i>Applied Physics Letters</i> , 2000 , 76, 3212-3214 | 3.4 | 91 |
| 581 | Electronic structure of piezoelectric In _{0.2} Ga _{0.8} N quantum dots in GaN calculated using a tight-binding method. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002 , 15, 169-181 | 3 | 89 |
| 580 | High-efficiency InAs/GaAs quantum dot solar cells by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2012 , 100, 193905 | 3.4 | 88 |
| 579 | Selective-area growth of thin GaN nanowires by MOCVD. <i>Journal of Crystal Growth</i> , 2012 , 357, 58-61 | 1.6 | 87 |
| 578 | Topological photonic crystal nanocavity laser. <i>Communications Physics</i> , 2018 , 1, | 5.4 | 85 |
| 577 | Exciton and biexciton luminescence from single hexagonal GaN/AlN self-assembled quantum dots. <i>Applied Physics Letters</i> , 2004 , 85, 64-66 | 3.4 | 84 |
| 576 | Optical directional coupler based on Si-wire waveguides. <i>IEEE Photonics Technology Letters</i> , 2005 , 17, 585-587 | 2.2 | 81 |
| 575 | Detailed balance limit of the efficiency of multilevel intermediate band solar cells. <i>Applied Physics Letters</i> , 2011 , 98, 171108 | 3.4 | 80 |
| 574 | Active topological photonics. <i>Nanophotonics</i> , 2020 , 9, 547-567 | 6.3 | 78 |

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| 573 | P-117 Phase II study of combination chemotherapy of gemcitabine/S-1 with nafamostat mesilate for advanced unresectable pancreatic cancer. First report. <i>Annals of Oncology</i> , 2016 , 27, ii34 | 10.3 | 78 |
| 572 | Low-Threshold near-Infrared GaAs/AlGaAs Core/Shell Nanowire Plasmon Laser. <i>ACS Photonics</i> , 2015 , 2, 165-171 | 6.3 | 75 |
| 571 | Fabrication of GaAs quantum wires (~10 nm) by metalorganic chemical vapor selective deposition growth. <i>Applied Physics Letters</i> , 1993 , 63, 355-357 | 3.4 | 75 |
| 570 | An optical horn structure for single-photon source using quantum dots at telecommunication wavelength). <i>Journal of Applied Physics</i> , 2007 , 101, 081720 | 2.5 | 74 |
| 569 | Strong coupling between a photonic crystal nanobeam cavity and a single quantum dot. <i>Applied Physics Letters</i> , 2011 , 98, 173104 | 3.4 | 73 |
| 568 | Room-temperature lasing oscillation in an InGaN self-assembled quantum dot laser. <i>Applied Physics Letters</i> , 1999 , 75, 2605-2607 | 3.4 | 73 |
| 567 | Second quantized state lasing of a current pumped single quantum well laser. <i>Applied Physics Letters</i> , 1986 , 49, 1689-1691 | 3.4 | 72 |
| 566 | Dose-dependent mixing of AlAs-GaAs superlattices by Si ion implantation. <i>Applied Physics Letters</i> , 1986 , 49, 701-703 | 3.4 | 71 |
| 565 | Photon lifetime dependence of modulation efficiency and K factor in 1.3 μ m self-assembled InAs/GaAs quantum-dot lasers: Impact of capture time and maximum modal gain on modulation bandwidth. <i>Applied Physics Letters</i> , 2004 , 85, 4145-4147 | 3.4 | 70 |
| 564 | Size-dependent radiative decay time of excitons in GaN/AlN self-assembled quantum dots. <i>Applied Physics Letters</i> , 2003 , 83, 984-986 | 3.4 | 70 |
| 563 | All MBE grown InAs/GaAs quantum dot lasers on on-axis Si (001). <i>Optics Express</i> , 2018 , 26, 11568-11576 | 3.3 | 68 |
| 562 | Artificial control of optical gain polarization by stacking quantum dot layers. <i>Applied Physics Letters</i> , 2006 , 88, 211106 | 3.4 | 68 |
| 561 | First demonstration of high density optical interconnects integrated with lasers, optical modulators, and photodetectors on single silicon substrate. <i>Optics Express</i> , 2011 , 19, B159-65 | 3.3 | 67 |
| 560 | Progress in quantum-dot single photon sources for quantum information technologies: A broad spectrum overview. <i>Applied Physics Reviews</i> , 2020 , 7, 021309 | 17.3 | 66 |
| 559 | Influence of strain relaxation of the Al _x Ga _{1-x} N barrier on transport properties of the two-dimensional electron gas in modulation-doped Al _x Ga _{1-x} N/GaN heterostructures. <i>Applied Physics Letters</i> , 2000 , 76, 2746-2748 | 3.4 | 66 |
| 558 | Electrically pumped 1.3 microm room-temperature InAs/GaAs quantum dot lasers on Si substrates by metal-mediated wafer bonding and layer transfer. <i>Optics Express</i> , 2010 , 18, 10604-8 | 3.3 | 65 |
| 557 | Lasing Emission from an In _{0.1} Ga _{0.9} N Vertical Cavity Surface Emitting Laser. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, L1424-L1426 | 1.4 | 65 |
| 556 | Kondo effect in a semiconductor quantum dot coupled to ferromagnetic electrodes. <i>Applied Physics Letters</i> , 2007 , 91, 232105 | 3.4 | 63 |

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| 555 | Near-field magneto-optical spectroscopy of single self-assembled InAs quantum dots. <i>Applied Physics Letters</i> , 1998 , 73, 517-519 | 3-4 | 63 |
| 554 | Low-voltage-operating complementary inverters with C60 and pentacene transistors on glass substrates. <i>Applied Physics Letters</i> , 2007 , 91, 053505 | 3-4 | 62 |
| 553 | 1.5- μ m-wavelength light guiding in waveguides in square-lattice-of-rod photonic crystal slab. <i>Applied Physics Letters</i> , 2004 , 84, 4298-4300 | 3-4 | 62 |
| 552 | Photon correlation studies of single GaN quantum dots. <i>Applied Physics Letters</i> , 2005 , 87, 051916 | 3-4 | 62 |
| 551 | Single Photons from a Hot Solid-State Emitter at 350 K. <i>ACS Photonics</i> , 2016 , 3, 543-546 | 6-3 | 61 |
| 550 | Organic/inorganic hybrid complementary circuits based on pentacene and amorphous indium gallium zinc oxide transistors. <i>Applied Physics Letters</i> , 2008 , 93, 213505 | 3-4 | 61 |
| 549 | Ultraclean Single Photon Emission from a GaN Quantum Dot. <i>Nano Letters</i> , 2017 , 17, 2902-2907 | 11-5 | 59 |
| 548 | Molecular analysis of <i>Clostridium difficile</i> at a university teaching hospital in Japan: a shift in the predominant type over a five-year period. <i>European Journal of Clinical Microbiology and Infectious Diseases</i> , 2007 , 26, 695-703 | 5-3 | 59 |
| 547 | X-chromosomal localization of mammalian Y-linked genes in two XO species of the Ryukyu spiny rat. <i>Cytogenetic and Genome Research</i> , 2002 , 99, 303-9 | 1-9 | 58 |
| 546 | Recombination lifetime of carriers in GaAs-GaAlAs quantum wells near room temperature. <i>Applied Physics Letters</i> , 1985 , 46, 519-521 | 3-4 | 58 |
| 545 | First Demonstration of Athermal Silicon Optical Interposers With Quantum Dot Lasers Operating up to 125 °C. <i>Journal of Lightwave Technology</i> , 2015 , 33, 1223-1229 | 4 | 57 |
| 544 | Anharmonic decay of confined optical phonons in quantum dots. <i>Physical Review B</i> , 1998 , 57, 12285-12290 | 3-5 | 57 |
| 543 | . <i>IEEE Journal of Quantum Electronics</i> , 2007 , 43, 1129-1139 | 2 | 56 |
| 542 | Shell structures in self-assembled InAs quantum dots probed by lateral electron tunneling structures. <i>Applied Physics Letters</i> , 2005 , 87, 203109 | 3-4 | 56 |
| 541 | Non-classical Photon Emission from a Single InAs/InP Quantum Dot in the 1.3- μ m Optical-Fiber Band. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, L993-L995 | 1-4 | 56 |
| 540 | Fabrication of GaAs arrowhead-shaped quantum wires by metalorganic chemical vapor deposition selective growth. <i>Applied Physics Letters</i> , 1993 , 62, 49-51 | 3-4 | 55 |
| 539 | Exciton fine-structure splitting in GaN/AlN quantum dots. <i>Physical Review B</i> , 2010 , 81, | 3-3 | 54 |
| 538 | Threshold voltage control of bottom-contact n-channel organic thin-film transistors using modified drain/source electrodes. <i>Applied Physics Letters</i> , 2009 , 94, 083310 | 3-4 | 54 |

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| 537 | Optical linewidths in an individual quantum dot. <i>Physical Review B</i> , 1999 , 60, 1915-1920 | 3-3 | 54 |
| 536 | GaAs quantum dots with lateral dimension of 25 nm fabricated by selective metalorganic chemical vapor deposition growth. <i>Applied Physics Letters</i> , 1994 , 64, 2495-2497 | 3-4 | 53 |
| 535 | A Nanowire-Based Plasmonic Quantum Dot Laser. <i>Nano Letters</i> , 2016 , 16, 2845-50 | 11.5 | 53 |
| 534 | Occupation of the double subbands by the two-dimensional electron gas in the triangular quantum well at Al _x Ga _{1-x} N/GaN heterostructures. <i>Physical Review B</i> , 2000 , 62, R7739-R7742 | 3-3 | 52 |
| 533 | Polarized photoluminescence spectroscopy of single self-assembled InAs quantum dots. <i>Physical Review B</i> , 1998 , 58, R10147-R10150 | 3-3 | 52 |
| 532 | Single-photon emission at 1.5 ħ from an InAs/InP quantum dot with highly suppressed multi-photon emission probabilities. <i>Applied Physics Letters</i> , 2016 , 109, 132106 | 3-4 | 52 |
| 531 | Hybrid p-n junction light-emitting diodes based on sputtered ZnO and organic semiconductors. <i>Applied Physics Letters</i> , 2009 , 95, 253303 | 3-4 | 51 |
| 530 | Narrow photoluminescence linewidth (. <i>Applied Physics Letters</i> , 2004 , 84, 2817-2819 | 3-4 | 51 |
| 529 | Near-field coherent excitation spectroscopy of InGaAs/GaAs self-assembled quantum dots. <i>Applied Physics Letters</i> , 2000 , 76, 3887-3889 | 3-4 | 51 |
| 528 | Enhanced and inhibited spontaneous emission in GaAs/AlGaAs vertical microcavity lasers with two kinds of quantum wells. <i>Applied Physics Letters</i> , 1991 , 58, 2339-2341 | 3-4 | 51 |
| 527 | Enhancement of carbon nanotube photoluminescence by photonic crystal nanocavities. <i>Applied Physics Letters</i> , 2012 , 101, 141124 | 3-4 | 50 |
| 526 | Observation of enhanced photoluminescence from silicon photonic crystal nanocavity at room temperature. <i>Applied Physics Letters</i> , 2007 , 91, 211104 | 3-4 | 50 |
| 525 | Nonlinear-Optic Silicon-Nanowire Waveguides. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 6541-6545 | 1.4 | 50 |
| 524 | . <i>IEEE Photonics Technology Letters</i> , 1992 , 4, 682-685 | 2.2 | 50 |
| 523 | The electronic properties of DNA bases. <i>Small</i> , 2007 , 3, 1539-43 | 11 | 49 |
| 522 | MOCVD-grown InGaN-channel HEMT structures with electron mobility of over 1000cm ² /Vs. <i>Journal of Crystal Growth</i> , 2004 , 272, 278-284 | 1.6 | 49 |
| 521 | AlN air-bridge photonic crystal nanocavities demonstrating high quality factor. <i>Applied Physics Letters</i> , 2007 , 91, 051106 | 3-4 | 48 |
| 520 | Time-resolved dynamics in single InGaN quantum dots. <i>Applied Physics Letters</i> , 2003 , 83, 2674-2676 | 3-4 | 48 |

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| 519 | Control of optical polarization anisotropy in edge emitting luminescence of InAs/GaAs self-assembled quantum dots. <i>Applied Physics Letters</i> , 2004 , 84, 1820-1822 | 3-4 | 48 |
| 518 | Current-gain cutoff frequencies above 10 MHz for organic thin-film transistors with high mobility and low parasitic capacitance. <i>Applied Physics Letters</i> , 2009 , 95, 023503 | 3-4 | 46 |
| 517 | Spectral diffusion and its influence on the emission linewidths of site-controlled GaN nanowire quantum dots. <i>Physical Review B</i> , 2015 , 92, | 3-3 | 45 |
| 516 | Ultrafast energy relaxation in quantum dots through defect states: A lattice-relaxation approach. <i>Physical Review B</i> , 1997 , 56, 10423-10427 | 3-3 | 45 |
| 515 | Bottom-contact fullerene C60 thin-film transistors with high field-effect mobilities. <i>Applied Physics Letters</i> , 2008 , 93, 033313 | 3-4 | 45 |
| 514 | Transfer-printed single-photon sources coupled to wire waveguides. <i>Optica</i> , 2018 , 5, 691 | 8.6 | 44 |
| 513 | Unconventional quantum-confined Stark effect in a single GaN quantum dot. <i>Physical Review B</i> , 2006 , 73, | 3-3 | 44 |
| 512 | Fabrication of quantum wires and dots by MOCVD selective growth. <i>Solid-State Electronics</i> , 1994 , 37, 523-528 | 1.7 | 44 |
| 511 | Tight-binding analysis of energy-band structures in quantum wires. <i>Physical Review B</i> , 1991 , 43, 4732-4738 | 3.9 | 44 |
| 510 | Thresholdless quantum dot nanolaser. <i>Optics Express</i> , 2017 , 25, 19981-19994 | 3-3 | 43 |
| 509 | Transmission Experiment of Quantum Keys over 50 km Using High-Performance Quantum-Dot Single-Photon Source at 1.5 μm Wavelength. <i>Applied Physics Express</i> , 2010 , 3, 092802 | 2.4 | 43 |
| 508 | Femtosecond dynamics of semiconductor-microcavity polaritons in the nonlinear regime. <i>Solid State Communications</i> , 1996 , 97, 941-946 | 1.6 | 43 |
| 507 | Picosecond pulse generation (. <i>Applied Physics Letters</i> , 1987 , 51, 1295-1297 | 3-4 | 43 |
| 506 | Room temperature continuous wave operation of InAs/GaAs quantum dot photonic crystal nanocavity laser on silicon substrate. <i>Optics Express</i> , 2009 , 17, 7036-42 | 3-3 | 42 |
| 505 | Formation and optical properties of stacked GaN self-assembled quantum dots grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2004 , 85, 1262-1264 | 3-4 | 42 |
| 504 | Nearly diffraction-limited focusing of a fiber axicon microlens. <i>Review of Scientific Instruments</i> , 2003 , 74, 4969-4971 | 1.7 | 42 |
| 503 | Spatially and spectrally resolved imaging of GaAs quantum-dot structures using near-field optical technique. <i>Applied Physics Letters</i> , 1996 , 69, 827-829 | 3-4 | 42 |
| 502 | InAs/GaAs self-assembled quantum-dot lasers grown by metalorganic chemical vapor depositionEffects of postgrowth annealing on stacked InAs quantum dots. <i>Applied Physics Letters</i> , 2004 , 85, 1024-1026 | 3-4 | 41 |

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| 501 | Growth process and mechanism of nanometer-scale GaAs dot-structures using MOCVD selective growth. <i>Journal of Crystal Growth</i> , 1993 , 126, 707-717 | 1.6 | 41 |
| 500 | Active Q switching in a GaAs/AlGaAs multiquantum well laser with an intracavity monolithic loss modulator. <i>Applied Physics Letters</i> , 1986 , 48, 561-563 | 3.4 | 41 |
| 499 | Exciton acoustic-phonon coupling in single GaN/AlN quantum dots. <i>Physical Review B</i> , 2012 , 85, | 3.3 | 40 |
| 498 | Demonstration of 12.5-Gbps optical interconnects integrated with lasers, optical splitters, optical modulators and photodetectors on a single silicon substrate. <i>Optics Express</i> , 2012 , 20, B256-63 | 3.3 | 40 |
| 497 | Site-controlled formation of InAs/GaAs quantum-dot-in-nanowires for single photon emitters. <i>Applied Physics Letters</i> , 2012 , 100, 263101 | 3.4 | 40 |
| 496 | Atomistic insights for InAs quantum dot formation on GaAs(001) using STM within a MBE growth chamber. <i>Small</i> , 2006 , 2, 386-9 | 11 | 40 |
| 495 | Single-photon emission from cubic GaN quantum dots. <i>Applied Physics Letters</i> , 2014 , 104, 011101 | 3.4 | 39 |
| 494 | High density InAs/GaAs quantum dots with enhanced photoluminescence intensity using antimony surfactant-mediated metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , 2006 , 89, 183124 | 3.4 | 39 |
| 493 | Fabrication of InAs quantum dots on InP(100) by metalorganic vapor-phase epitaxy for 1.55 μ m optical device applications. <i>Applied Physics Letters</i> , 2004 , 85, 4331 | 3.4 | 39 |
| 492 | Emission of Linearly Polarized Single Photons from Quantum Dots Contained in Nonpolar, Semipolar, and Polar Sections of Pencil-Like InGaN/GaN Nanowires. <i>ACS Photonics</i> , 2017 , 4, 657-664 | 6.3 | 38 |
| 491 | High conductance bottom-contact pentacene thin-film transistors with gold-nickel adhesion layers. <i>Applied Physics Letters</i> , 2010 , 97, 033306 | 3.4 | 37 |
| 490 | Light emission from zero-dimensional excitons/Photoluminescence from quantum wells in strong magnetic fields. <i>Applied Physics Letters</i> , 1985 , 46, 83-85 | 3.4 | 37 |
| 489 | Manifestation of unconventional biexciton states in quantum dots. <i>Nature Communications</i> , 2014 , 5, 5721 | 17.4 | 36 |
| 488 | Vacuum Rabi splitting with a single quantum dot embedded in a H1 photonic crystal nanocavity. <i>Applied Physics Letters</i> , 2009 , 94, 033102 | 3.4 | 36 |
| 487 | Area-controlled growth of InAs quantum dots and improvement of density and size distribution. <i>Applied Physics Letters</i> , 2000 , 77, 3382-3384 | 3.4 | 36 |
| 486 | Photoluminescence studies of GaAs quantum wires with quantum confined Stark effect. <i>Applied Physics Letters</i> , 1997 , 70, 646-648 | 3.4 | 35 |
| 485 | Density Control of GaSb/GaAs Self-assembled Quantum Dots (~25nm) Grown by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, L203-L205 | 1.4 | 35 |
| 484 | Room temperature continuous wave lasing in InAs quantum-dot microdisks with air cladding. <i>Optics Express</i> , 2005 , 13, 1615-20 | 3.3 | 35 |

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|-----|---|------|----|
| 483 | Low threshold current operation of self-assembled InAs/GaAs quantum dot lasers by metal organic chemical vapour deposition. <i>Electronics Letters</i> , 2003 , 39, 1130 | 1.1 | 35 |
| 482 | One-dimensional exciton diffusion in GaAs quantum wires. <i>Applied Physics Letters</i> , 1995 , 67, 1535-1537 | 3.4 | 35 |
| 481 | Enhanced modulation bandwidth of GaAlAs double heterostructure lasers in high magnetic fields: Dynamic response with quantum wire effects. <i>Applied Physics Letters</i> , 1985 , 47, 1142-1144 | 3.4 | 35 |
| 480 | Two-dimensional photonic crystal resist membrane nanocavity embedding colloidal dot-in-a-rod nanocrystals. <i>Nano Letters</i> , 2008 , 8, 260-4 | 11.5 | 34 |
| 479 | Time-of-Flight Measurement of Lateral Carrier Mobility in Organic Thin Films. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, 2326-2329 | 1.4 | 34 |
| 478 | Area Density Control of Quantum-Size InGaAs/Ga(Al)As Dots by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 1994 , 33, L1634-L1637 | 1.4 | 34 |
| 477 | High-Q design of semiconductor-based ultrasmall photonic crystal nanocavity. <i>Optics Express</i> , 2010 , 18, 8144-50 | 3.3 | 33 |
| 476 | Spin-related current suppression in a semiconductor quantum dot spin-diode structure. <i>Physical Review Letters</i> , 2009 , 102, 236806 | 7.4 | 33 |
| 475 | Demonstration of transverse-magnetic dominant gain in quantum dot semiconductor optical amplifiers. <i>Applied Physics Letters</i> , 2008 , 92, 101108 | 3.4 | 33 |
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